Product data sheet

1. General description

Dual ultrafast power diodes in a SOT186A (TO-220F) isolated plastic package. These diodes are rugged with a guaranteed electrostatic discharge voltage capability.

2. Features and benefits

- Fast switching
- · Guaranteed ESD capability
- · High thermal cycling performance
- · Isolated package
- Low on-state losses
- Soft recovery minimizes power-consuming oscillations

3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_R	reverse voltage	DC	-	-	200	V
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_h \le 92$ °C; SQW; per diode	-	-	10	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	-	50	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; per diode	-	-	55	Α
Static chara	cteristics					
V _F forward voltage	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 4</u>	-	0.95	1.1	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 4</u>	-	8.0	0.895	V
		I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.25	V
Dynamic cha	aracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5	-	15	25	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	A1
2	K	cathode		A1 [N] A2
3	A2	anode 2		K sym125
mb	n.c.	mounting base; isolated	1 2 3 TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BYQ28X-200E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A		

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V_{R}	reverse voltage	DC	-	200	V
I _{O(AV)}	average output current	δ = 0.5 ; T _h \leq 92 °C; SQW; Fig. 1; Fig. 2	-	10	Α
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_h \le$ 92 °C; SQW; per diode	-	10	A
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; SIN; per diode	-	50	Α
	forward current	t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN; per diode	-	55	Α
I _{RRM}	repetitive peak reverse current	$\delta = 0.001 \; ; t_p = 2 \; \mu s$	-	0.2	Α
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	-	0.2	A
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C
Electrostatic di	scharge		,		
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins	-	8	kV

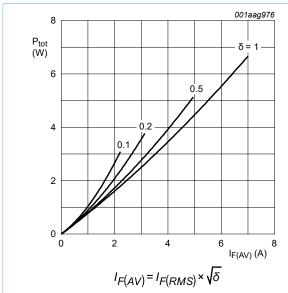


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

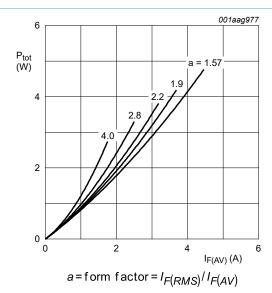
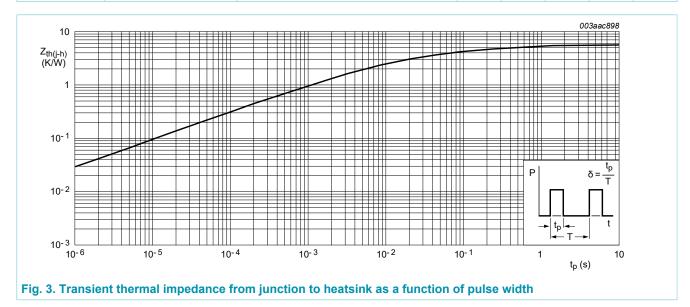


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 3	-	-	5.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	55	-	K/W



9. Isolation characteristics

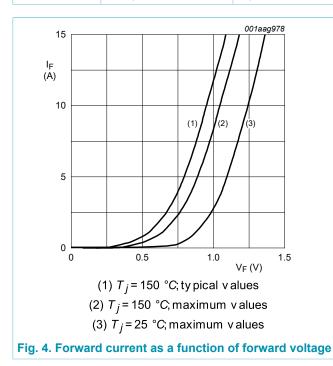
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz < f < 60 Hz; sinusoidal waveform; relative humidity < 65 %; clean and dust free; from all terminals to external heatsink	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF
		from cathode to external heatsink; f = 1 MHz	-	10	-	pF

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mi	т Тур	Max	Unit
Static chara	acteristics			,		7
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 4</u>	-	0.95	1.1	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
		I _F = 10 A; T _j = 25 °C; <u>Fig. 4</u>	-	1.1	1.25	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-	2	10	μA
		V _R = 200 V; T _j = 100 °C	-	0.1	0.2	mA
Dynamic ch	naracteristics			·		
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5	-	15	25	ns
		I_F = 0.5 A; I_R = 1 A; T_j = 25 °C; step recovery; measured at I_R = 0.25 A; Fig. 6	-	10	20	ns
I _{RM}	peak reverse recovery current	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $\frac{\text{Fig. 5}}{}$	-	0.4	0.7	A
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; $\frac{\text{Fig. 5}}{}$	-	4	9	μC
V_{FR}	forward recovery voltage	$I_F = 1 \text{ A}$; $dI_F/dt = 10 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	1	-	V



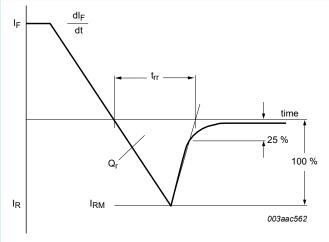
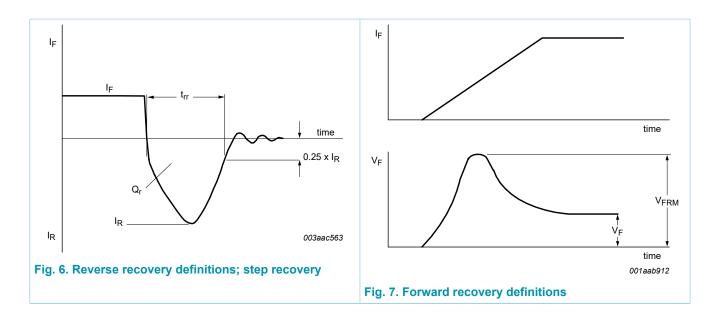


Fig. 5. Reverse recovery definitions; ramp recovery

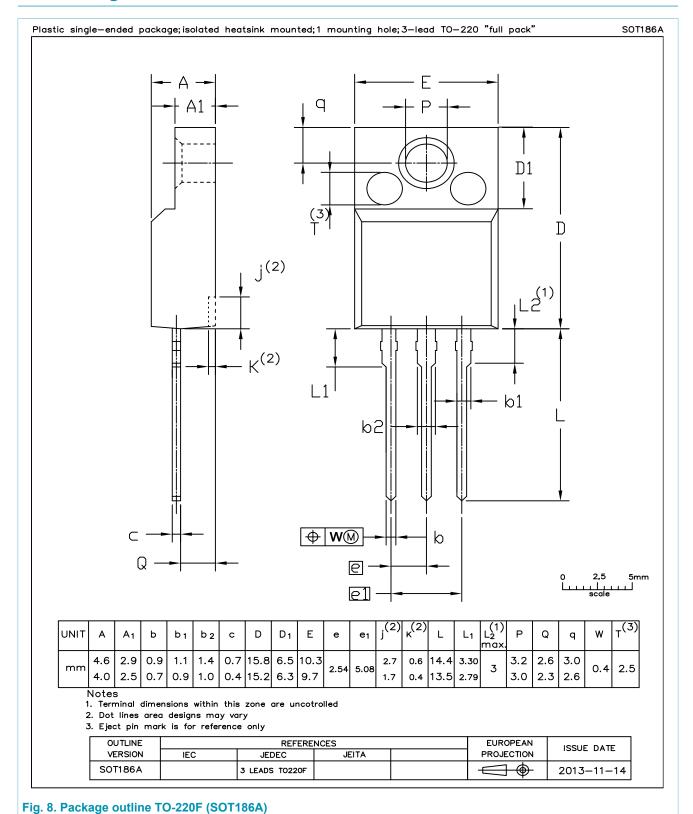
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Dual ultrafast power diodes



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11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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